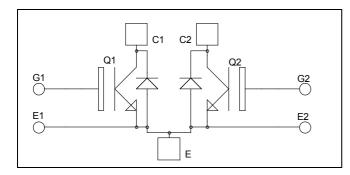


**Dual common source** Trench + Field Stop IGBT3 **Power Module** 



## G С E E2 G2

# APTGT300DU60G

## $V_{CES} = 600V$ $I_{\rm C} = 300 {\rm A}$ @ Tc = 80°C

#### Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

#### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop -
    - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
  - Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

#### **Benefits**

- Stable temperature behavior •
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile .
- **RoHS** Compliant

### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		600	V
I <sub>C</sub>	Continuous Collector Current	$T_C = 25^{\circ}C$	430	
	Continuous Conector Current	$T_C = 80^{\circ}C$	300	Α
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	500	
V <sub>GE</sub>	Gate – Emitter Voltage		±20	V
P <sub>D</sub>	Maximum Power Dissipation	$T_C = 25^{\circ}C$	1150	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	600A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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## All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				350	μA
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 300A$	$T_j = 25^{\circ}C$		1.4	1.8	V
			$T_{j} = 150^{\circ}C$		1.5		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5 \text{ mA}$		5.0	5.8	6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				500	nA

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			24			
Coes	Output Capacitance				1.5		nF	
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz		0.75				
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switch	ning (25°C)		115		ns	
T <sub>r</sub>	Rise Time	$V_{GE} = \pm 15V$			45			
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 300A$			200			
$T_{\rm f}$	Fall Time	$R_{G} = 1.8\Omega$			55			
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 300A$			120		ns	
Tr	Rise Time				50			
T <sub>d(off)</sub>	Turn-off Delay Time				250			
T <sub>f</sub>	Fall Time	$R_G = 1.8\Omega$		70				
Г	T	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$	$V_{CE} = +15V$ T	$T_i = 25^{\circ}C$		1.5		<b>T</b>
Eon	Turn on Energy		$T_{j} = 150^{\circ}C$		2.7		mJ	
Б	$ E_{off}  \text{Turn off Energy} \qquad I_{C} = 300 \text{A} \\ R_{G} = 1.8 \Omega $		$T_j = 25^{\circ}C$		8.55		mI	
$\mathbf{L}_{\mathrm{off}}$		$R_G = 1.8\Omega$	$T_{j} = 150^{\circ}C$		10.5		mJ	

### Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			600			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			150 400	μΑ
I <sub>F</sub>	DC Forward Current		$T_j = 130 \text{ C}$ $T_c = 80^{\circ}\text{C}$		300	400	А
V <sub>F</sub>	Diode Forward Voltage	$I_{\rm F} = 300 {\rm A}$ $V_{\rm GE} = 0 {\rm V}$	$T_i = 25^{\circ}C$		1.5	1.9	V
v <sub>F</sub>	Didde Forward Voltage		$T_{i} = 150^{\circ}C$		1.4		v
t <sub>rr</sub>	Reverse Recovery Time	$I_{F} = 300A$ $V_{R} = 300V$ $di/dt = 3100A/\mu s$	$T_j = 25^{\circ}C$		130		ns
ι <sub>rr</sub>			$T_{j} = 150^{\circ}C$		225		
Q <sub>rr</sub>	Reverse Recovery Charge		$T_j = 25^{\circ}C$		13.5		шС
			$T_{j} = 150^{\circ}C$		28.5		μC
Er	Reverse Recovery Energy		$T_j = 25^{\circ}C$		3.5		mJ
			$T_{j} = 150^{\circ}C$		7.1		1113

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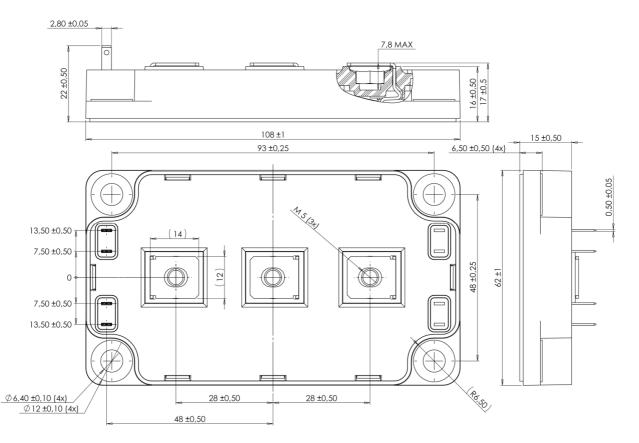


## APTGT300DU60G

## Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance IGBT Diode				0.13	°C/W	
<b>R</b> <sub>th</sub> JC			Diode			0.21	C/ W
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		175	
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

### SP6 Package outline (dimensions in mm)



See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

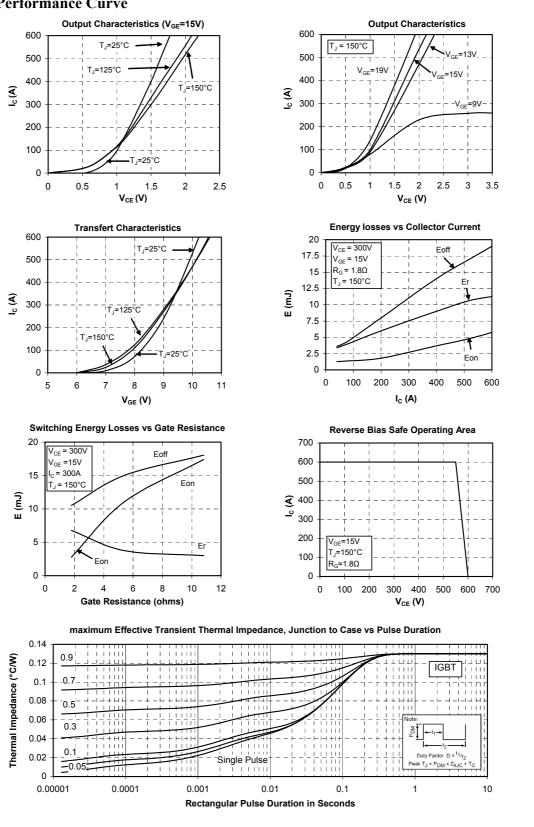
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#### **Typical Performance Curve**





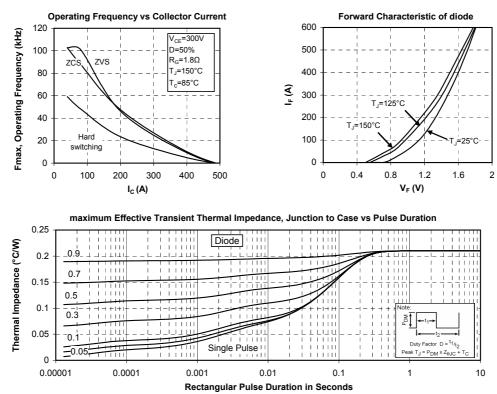
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